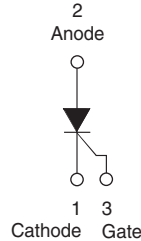


Phase Control SCR, 8 A



D²PAK



FEATURES

- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Compliant to RoHS directive 2002/95/EC
- Halogen-free according to IEC 61249-2-21 definition
- Designed and qualified for industrial level



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Input rectification and crow-bar (soft start)
- Vishay input diodes, switches and output rectifiers which are available in identical package outlines

DESCRIPTION

The VS-12TTS08SPbF High Voltage Series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

PRODUCT SUMMARY	
V_T at 8 A	< 1.2 V
I_{TSM}	140 A
V_{RRM}	800 V

OUTPUT CURRENT IN TYPICAL APPLICATIONS			
APPLICATIONS	SINGLE-PHASE BRIDGE	THREE-PHASE BRIDGE	UNITS
Capacitive input filter $T_A = 55\text{ °C}$, $T_J = 125\text{ °C}$, common heatsink of 1 °C/W	13.5	17	A

MAJOR RATINGS AND CHARACTERISTICS			
PARAMETER	TEST CONDITIONS	VALUES	UNITS
$I_{T(AV)}$	Sinusoidal waveform	8	A
$I_{T(RMS)}$		12.5	
V_{RRM}/V_{DRM}		800	V
I_{TSM}		140	A
V_T	8 A, $T_J = 25\text{ °C}$	1.2	V
dV/dt		150	V/ μ s
dI/dt		100	A/ μ s
T_J	Range	- 40 to 125	°C

VOLTAGE RATINGS			
PART NUMBER	V_{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V	V_{DRM} , MAXIMUM PEAK DIRECT VOLTAGE V	I_{RRM}/I_{DRM} AT 125 °C mA
VS-12TTS08SPbF	800	800	1.0

VS-12TTS08SPbF High Voltage Series



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ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum average on-state current	$I_{T(AV)}$	$T_C = 108\text{ }^\circ\text{C}$, 180° conduction, half sine wave	8	A	
Maximum RMS on-state current	$I_{T(RMS)}$		12.5		
Maximum peak one-cycle non-repetitive surge current	I_{TSM}	10 ms sine pulse, rated V_{RRM} applied, $T_J = 125\text{ }^\circ\text{C}$	120		
		10 ms sine pulse, no voltage reapplied, $T_J = 125\text{ }^\circ\text{C}$	140		
Maximum I^2t for fusing	I^2t	10 ms sine pulse, rated V_{RRM} applied, $T_J = 125\text{ }^\circ\text{C}$	72	A^2s	
		10 ms sine pulse, no voltage reapplied, $T_J = 125\text{ }^\circ\text{C}$	100		
Maximum $I^2\sqrt{t}$ for fusing	$I^2\sqrt{t}$	$t = 0.1\text{ ms to }10\text{ ms}$, no voltage reapplied, $T_J = 125\text{ }^\circ\text{C}$	1000	$A^2\sqrt{s}$	
Maximum on-state voltage drop	V_{TM}	8 A, $T_J = 25\text{ }^\circ\text{C}$	1.2	V	
On-state slope resistance	r_t	$T_J = 125\text{ }^\circ\text{C}$	16.2	$m\Omega$	
Threshold voltage	$V_{T(TO)}$		0.87	V	
Maximum reverse and direct leakage current	I_{RM}/I_{DM}	$V_R = \text{Rated } V_{RRM}/V_{DRM}$	$T_J = 25\text{ }^\circ\text{C}$	0.05	mA
			$T_J = 125\text{ }^\circ\text{C}$	1.0	
Typical holding current	I_H	Anode supply = 6 V, resistive load, initial $I_T = 1\text{ A}$	30		
Maximum latching current	I_L	Anode supply = 6 V, resistive load	50		
Maximum rate of rise of off-state voltage	dV/dt	$T_J = 25\text{ }^\circ\text{C}$	150	$V/\mu s$	
Maximum rate of rise of turned-on current	dI/dt		100	$A/\mu s$	

TRIGGERING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum peak gate power	P_{GM}		8.0	W
Maximum average gate power	$P_{G(AV)}$		2.0	
Maximum peak positive gate current	+ I_{GM}		1.5	A
Maximum peak negative gate voltage	- V_{GM}		10	V
Maximum required DC gate current to trigger	I_{GT}	Anode supply = 6 V, resistive load, $T_J = -65\text{ }^\circ\text{C}$	20	mA
		Anode supply = 6 V, resistive load, $T_J = 25\text{ }^\circ\text{C}$	15	
		Anode supply = 6 V, resistive load, $T_J = 125\text{ }^\circ\text{C}$	10	
Maximum required DC gate voltage to trigger	V_{GT}	Anode supply = 6 V, resistive load, $T_J = -65\text{ }^\circ\text{C}$	1.2	V
		Anode supply = 6 V, resistive load, $T_J = 25\text{ }^\circ\text{C}$	1	
		Anode supply = 6 V, resistive load, $T_J = 125\text{ }^\circ\text{C}$	0.7	
Maximum DC gate voltage not to trigger	V_{GD}	$T_J = 125\text{ }^\circ\text{C}$, $V_{DRM} = \text{Rated value}$	0.2	
Maximum DC gate current not to trigger	I_{GD}		0.1	mA

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Typical turn-on time	t_{gt}	$T_J = 25\text{ }^\circ\text{C}$	0.8	μs
Typical reverse recovery time	t_{rr}	$T_J = 125\text{ }^\circ\text{C}$	3	
Typical turn-off time	t_q		100	



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THERMAL AND MECHANICAL SPECIFICATIONS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction and storage temperature range	T_J, T_{Stg}		- 40 to 125	°C
Maximum thermal resistance, junction to case	R_{thJC}	DC operation	1.5	°C/W
Maximum thermal resistance, junction to ambient	R_{thJA}		62	
Typical thermal resistance, case to heatsink	R_{thCS}	Mounting surface, smooth and greased	0.5	
Approximate weight			2	g
			0.07	oz.
Mounting torque	minimum		6 (5)	kgf · cm (lbf · in)
	maximum		12 (10)	
Marking device		Case style D ² PAK (SMD-220)	12TTS08S	

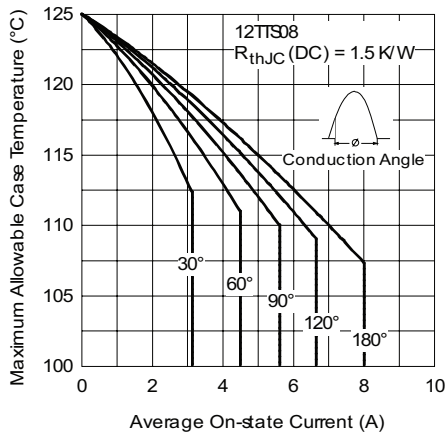


Fig. 1 - Current Rating Characteristics

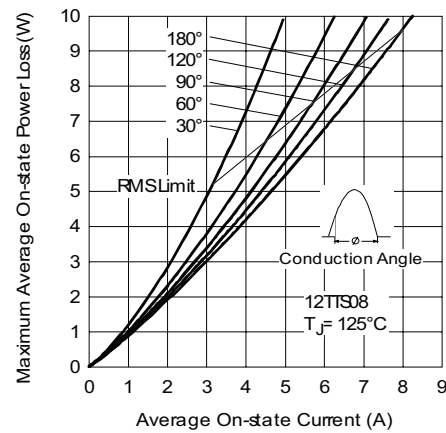


Fig. 3 - On-State Power Loss Characteristics

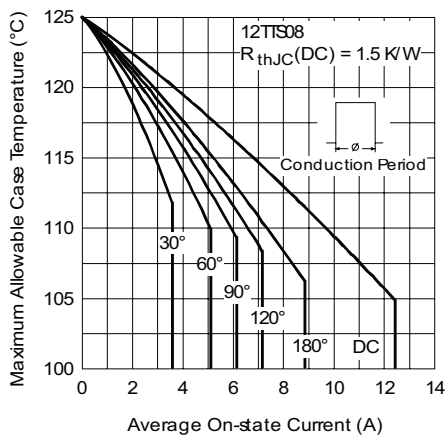


Fig. 2 - Current Rating Characteristics

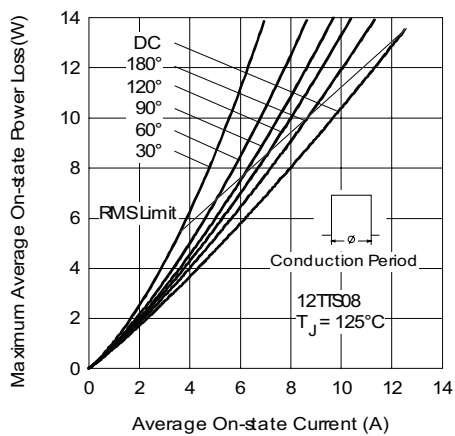


Fig. 4 - On-State Power Loss Characteristics

VS-12TTS08SPbF High Voltage Series

Vishay Semiconductors

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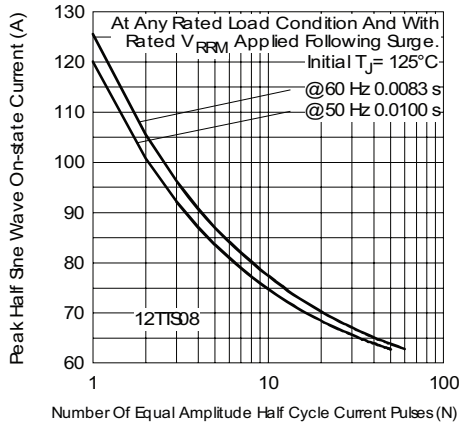


Fig. 5 - Maximum Non-Repetitive Surge Current

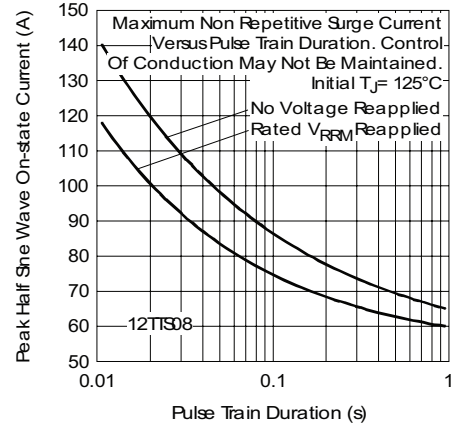


Fig. 6 - Maximum Non-Repetitive Surge Current

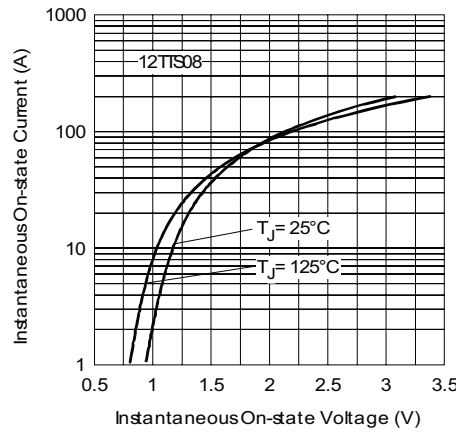


Fig. 7 - On-State Voltage Drop Characteristics

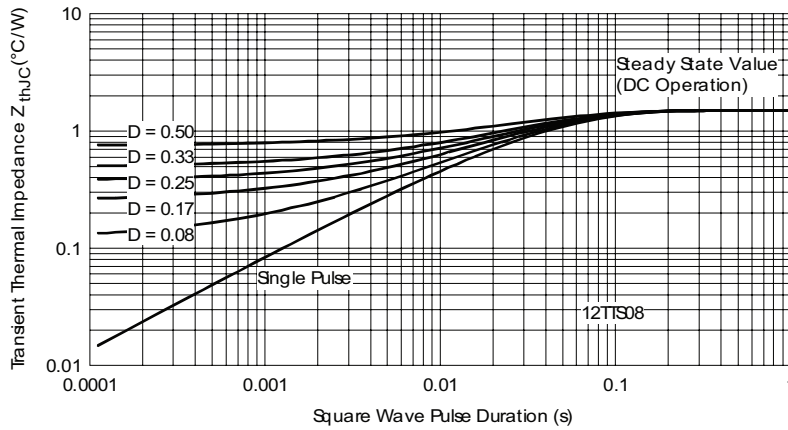


Fig. 8 - Thermal Impedance Z_{thJC} Characteristics

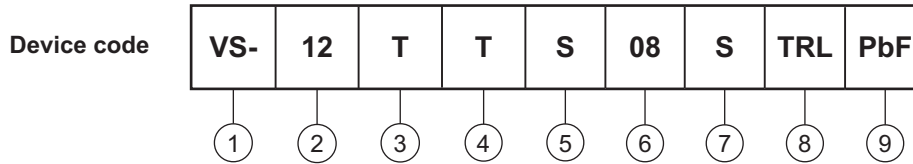


VS-12TTS08SPbF High Voltage Series

Phase Control SCR, 8 A

Vishay Semiconductors

ORDERING INFORMATION TABLE



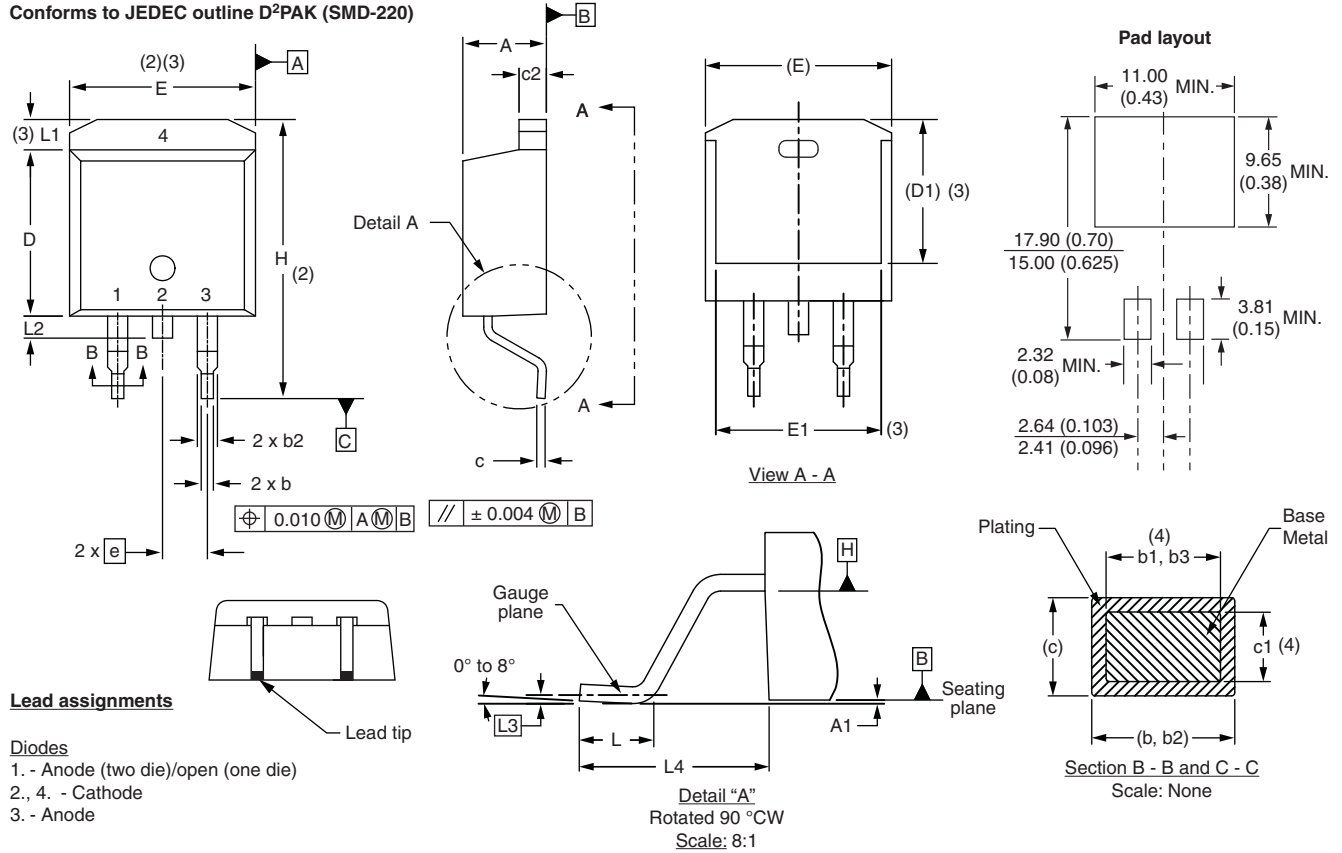
- 1** - HPP product suffix
- 2** - Current rating (12.5 A)
- 3** - Circuit configuration:
T = Single thyristor
- 4** - Package:
T = TO-220AC
- 5** - Type of silicon:
S = Standard recovery rectifier
- 6** - Voltage rating (08 = 800 V)
- 7** - S = TO-220 D²PAK (SMD-220) version
- 8** -
 - None = Tube
 - TRL = Tape and reel (left oriented)
 - TRR = Tape and reel (right oriented)
- 9** - PbF = Lead (Pb)-free

LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?95046
Part marking information	www.vishay.com/doc?95054
Packaging information	www.vishay.com/doc?95032

D²PAK

DIMENSIONS in millimeters and inches

Conforms to JEDEC outline D²PAK (SMD-220)



SYMBOL	MILLIMETERS		INCHES		NOTES	SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.			MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	0.160	0.190		D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010		E	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039		E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4	e	2.54 BSC		0.100 BSC		
b2	1.14	1.78	0.045	0.070		H	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4	L	1.78	2.79	0.070	0.110	
c	0.38	0.74	0.015	0.029		L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4	L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065		L3	0.25 BSC		0.010 BSC		
D	8.51	9.65	0.335	0.380	2	L4	4.78	5.28	0.188	0.208	

Notes

- Dimensioning and tolerancing per ASME Y14.5 M-1994
- Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- Thermal pad contour optional within dimension E, L1, D1 and E1
- Dimension b1 and c1 apply to base metal only
- Datum A and B to be determined at datum plane H
- Controlling dimension: inch
- Outline conforms to JEDEC outline TO-263AB



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